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Zhang	Xionsen	College of Automation Engineering, Nanjing University of Aeronautics and Astronautics	China
Zhang	Yi	Infineon Semiconductors (Shenzhen) Company Limited	China
Zhang	Yichun	CRRC Zhuzhou Institute Co., Ltd	China
Zhao	Jia	Infineon Integrated Circuit (Beijing) Co., Ltd.	China
Zhao	Kai	Infineon Semiconductors (Shenzhen) Co. Ltd	China
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Zhao	Zhenbo	Infineon Technologies China Co., Ltd	China
Zheng	Jun	MACMIC SCIENCE&TECHNOLOGY CO., LTD	China
Zheng	Yanxuan	Electrical Engineering School of Beijing Jiaotong University	China
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Zhou	Hongwei	TBEA Xi'an Electric Technology Co., Ltd	China
Zhou	Ming	Infineon Semiconductor (Shenzhen) Co. Ltd.	China
Zhou	Wangjun	Zhuzhou CRRC Times Semiconductor Co., Ltd., State Key Laboratory of Power Semiconductor and Integration Technology	China
Zhou	Yuan	SABIC	China
Zhou	Yuming	Anhui University of Technology	China
Zhu	Liheng	Zhuzhou CRRC Times Semiconductor Co. Ltd	China
Zhu	Minglei	State Grid Anhui Electric Vehicle Service Co., Ltd	China
Zhu	Yongshuang	Infineon Semiconductors (Shenzhen) Company Limited	China
Zhu	Yujia	Harbin Institute of Technology	China
Zhuo	Yuteng	Shanghai Lingang Power Electronics Research Co., Ltd.	China
Zou	Chunbao	Yunnan Energy Investment Co., Ltd. of Three Gorges Corporation	China
Zou	Xinyu	Institute of Electrical Engineering of the Chinese Academy of Sciences, University of Chinese Academy of Sciences	China